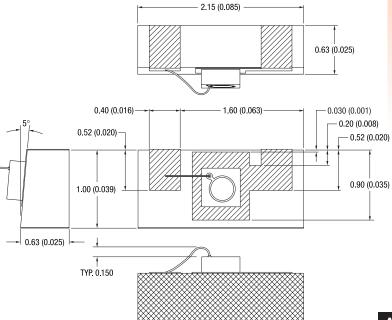
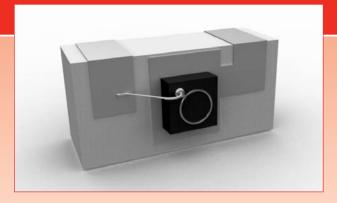
■FCI-InGaAs-XXX-ACER

High Speed InGaAs Photodiodes Mounted on Wedge Ceramic Packages

FCI-InGaAs-XXX-ACER with active area sizes of 70µm, 120µm, 300µm, 400µm and 500µm is part of OSI Optoelectronics's high speed IR sensitive photodiodes mounted on angled ceramic substrates. The ceramic substrate with an angled surface by 5° greatly reduces the back reflection. The chips can be epoxy/eutectic mounted onto the angled ceramic substrate.





• APPLICATIONS

- High Speed Optical Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitor
- Instrumentation

• FEATURES

- 5° Angle Ceramic
- Low Noise
- High Responsivity
- High Speed
- Spectral Range 900nm to 1700nm

Notes:	
All units in millimeters (inches).	
 All devices are eutectic mounted with tolerance of ±50µm. 	

Absolute Maximum Ratings										
PARAMETERS	SYMBOL	MIN	MAX	UNITS						
Storage Temperature	T _{stg}	-40	+85	°C						
Operating Temperature	T _{op}	0	+70	°C						
Soldering Temperature	T _{sld}		+260	°C						

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PARAMETERS SYM	SYMBOL	BOL CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Active Area Diameter	AA_{ϕ}			70			120			300			400			500		
Responsivity	R_{λ}	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		μm
		λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		A/W
Capacitance	C _j	V _R = 5.0V		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	I _d	V _R = 5.0V		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_R = 5.0V,$ $R_L = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Revervse Voltage					20			20			15			15			15	V
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz